Freeform Search

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Database:	US Pre-Grant Publication Full-Text Database						
	US Patents Full-Text Database						
	US OCR Full-Text Database						
	: EPO Abstracts Database						
	JPO Abstracts Database						
	Derwent World Patents Index						
	IBM Technical Disclosure Bulletins						
Term:	L16 and ("single crystal extrinsic" near5 (base						
	near3 transistor))						
D:1							
Display:	10 Documents in <u>Display Format</u> : T Starting with Number 1						
Generate: C Hit List C Hit Count C Side by Side C Image							
NA.							
Search Clear Interrupt							
Sagrah Uistony							
Search History							

DATE: Thursday, August 12, 2004 Printable Copy Create Case

Set Name		Hit Count	
side by side			result set
	SPT; PLUR=YES; OP=OR		
<u>L21</u>	L16 and ("single crystal extrinsic" near5 (base near3 transistor))	0	<u>L21</u>
<u>L20</u>	L16 and ("single crystal extrinsic" near5 (base near3 transistor))	0	<u>L20</u>
<u>L19</u>	L16 and ("single crystal intrinsic" near5 (base near3 transistor))	0	<u>L19</u>
<u>L18</u>	L16 and ("single crystal" near5 (base near3 transistor))	10	<u>L18</u>
<u>L17</u>	L16 and ("single crystal" near5 base)	46	<u>L17</u>
<u>L16</u>	L15 and soi	1468	<u>L16</u>
<u>L15</u>	"bipolar transistor"	28084	<u>L15</u>
<u>L14</u>	bipolar	59573	<u>L14</u>
DB=TL	OBD; PLUR=YES; OP=OR		
<u>L13</u>	L12	0	<u>L13</u>
DB=DI	WPI; PLUR=YES; OP=OR		
<u>L12</u>	L11	0	<u>L12</u>
DB=JP	AB; PLUR=YES; OP=OR		
<u>L11</u>	L10	0	<u>L11</u>
DB=EF	PAB; PLUR=YES; OP=OR		
<u>L10</u>	L9	0	<u>L10</u>

DB=U	SOC; $PLUR=YES$; $OP=OR$		
<u>L9</u>	L8	0	<u>L9</u>
DB=P	GPB; PLUR=YES; OP=OR		
<u>L8</u>	L7	0	<u>L8</u>
DB=U	SPT; PLUR=YES; OP=OR		
<u>L7</u>	L6 and HDP	0	<u>L7</u>
<u>L6</u>	L4 and soi	5	<u>L6</u>
<u>L5</u>	L4 and traverse and longitudinal	1	<u>L5</u>
<u>L4</u>	transistor\$ same (isolation near5 TEOS)	33	<u>L4</u>
<u>L3</u>	NFET same (isolation near5 TEOS)	0	<u>L3</u>
<u>L2</u>	L1 and "first isolation" and "second isolation"	4	<u>L2</u>
L1	isolation same TEOS same HDP	76	T.1

END OF SEARCH HISTORY